

μ PA2737GR

P-channel MOSFET

-30 V, -11 A, $13 \text{ m}\Omega$

R07DS0869EJ0100 Rev.1.00 Aug 28, 2012

Description

The μ PA2737GR is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

Features

- $V_{DSS} = -30 \text{ V } (T_A = 25^{\circ}\text{C})$
- Low on-state resistance
 - --- $R_{DS(on)}$ = 13 mΩ MAX. (V_{GS} = -10 V, I_D = -11 A)
- 4.5 V Gate-drive available
- Small and surface mount package (Power SOP8)
- Pb-free and Halogen free



Power SOP8

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μ PA2737GR-E1-AT	Pure Sn	Tape 2500 p/reel	Power SOP8
μ PA2737GR-E2-AT			0.08 g TYP.

Absolute Maximum Ratings ($T_A = 25$ °C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V_{DSS}	-30	V
Gate to Source Voltage (V _{DS} = 0 V)	V_{GSS}	∓20	V
Drain Current (DC)	I _{D(DC)}	∓11	Α
Drain Current (pulse) *1	I _{D(pulse)}	∓110	Α
Total Power Dissipation *2	P _{T1}	1.1	W
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	2.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	−55 to +150	°C
Single Avalanche Current *3	I _{AS}	11	Α
Single Avalanche Energy *3	E _{AS}	12.1	mJ

Thermal Resistance

Channel to Ambient Thermal Resistance *2 R_{th(ch-A)} 114 °C/W

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

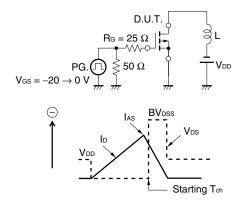
- *2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt
- *3. Starting $T_{ch} = 25$ °C, $V_{DD} = -15$ V, $R_G = 25$ Ω , $V_{GS} = -20 \rightarrow 0$ V, L = 100 μH

Electrical Characteristics (T_A = 25°C)

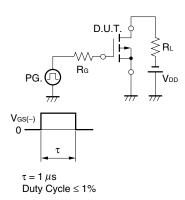
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			-1	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			∓100	nA	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	$V_{GS(off)}$	-1.0		-2.5	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	4.5			S	$V_{DS} = -10 \text{ V}, I_{D} = -5.5 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		9.7	13	mΩ	$V_{GS} = -10 \text{ V}, I_{D} = -11 \text{ A}$
Resistance *1	R _{DS(on)2}		17	25	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -11 \text{ A}$
Input Capacitance	C _{iss}		1750		pF	$V_{DS} = -10 \text{ V},$
Output Capacitance	Coss		850		pF	$V_{GS} = 0 V$,
Reverse Transfer Capacitance	C _{rss}		770		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		20		ns	$V_{DD} = -15 \text{ V}, I_D = -5.5 \text{ A},$
Rise Time	t _r		32		ns	$V_{GS} = -10 \text{ V},$
Turn-off Delay Time	t _{d(off)}		70		ns	$R_G = 10 \Omega$
Fall Time	t _f		55		ns	
Total Gate Charge	Q_{G}		45		nC	$V_{DD} = -24 \text{ V},$
Gate to Source Charge	Q_{GS}		2.5		nC	$V_{GS} = -10 \text{ V},$
Gate to Drain Charge	Q_{GD}		23		nC	I _D = -11 A
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.85		V	I _F = 11 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		49		ns	$I_F = 11 \text{ A}, V_{GS} = 0 \text{ V},$
Reverse Recovery Charge	Q _{rr}		48		nC	di/dt = 100 A/μs

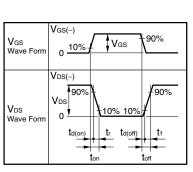
Note: *1. Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME





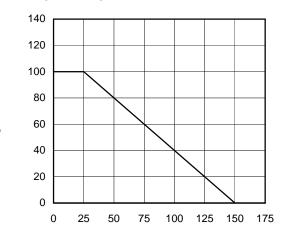
TEST CIRCUIT 3 GATE CHARGE

$$\begin{array}{c|c} D.U.T. \\ \hline \\ IG = -2 \text{ mA} \\ \hline \\ \hline \\ PG. \\ \hline \\ \end{array}$$

dT - Percentage of Rated Power - %

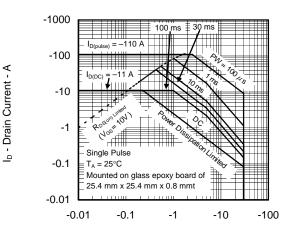
TYPICAL CHARACTERISTICS (T_A = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



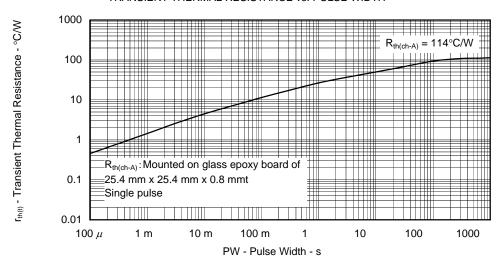
T_A - Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA

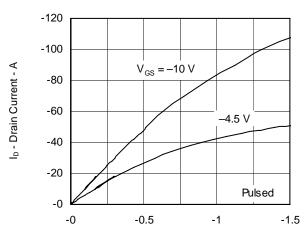


V_{DS} - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

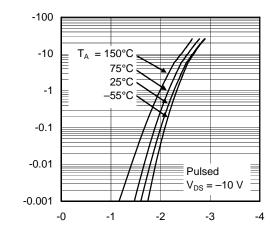


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

FORWARD TRANSFER CHARACTERISTICS

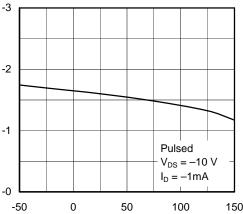


V_{GS} - Gate to Source Voltage - V

Ip - Drain Current - A

V_{GS(off)} - Gate to Source Cut-off Voltage - V

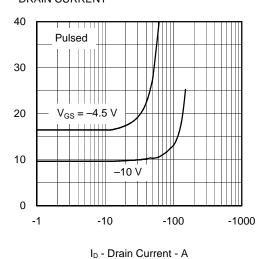
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



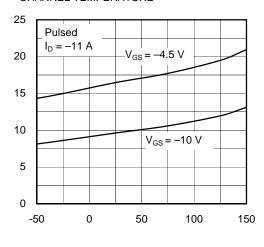
T_{ch} - Channel Temperature - °C

150

DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**

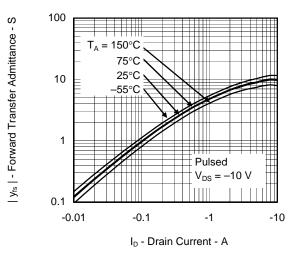


DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

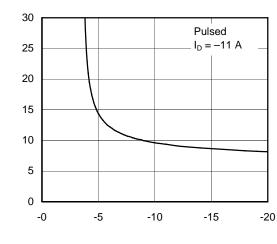


 T_{ch} - Channel Temperature - $^{\circ}C$

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

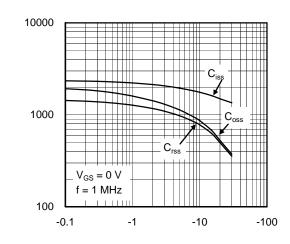


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



V_{GS} - Gate to Source Voltage - V

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

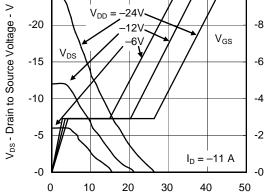
 $R_{\text{DS}(\text{on})}$ - Drain to Source On-state Resistance - $m\Omega$

R_{DS(on)} - Drain to Source On-state Resistance - mΩ

Ciss, Coss, Crss - Capacitance - pF

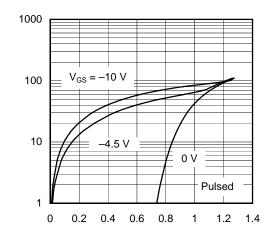
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

-25 V_{DD} = -24V



 $\ensuremath{\mathsf{Q}}_G$ - Gate Charge - nC

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



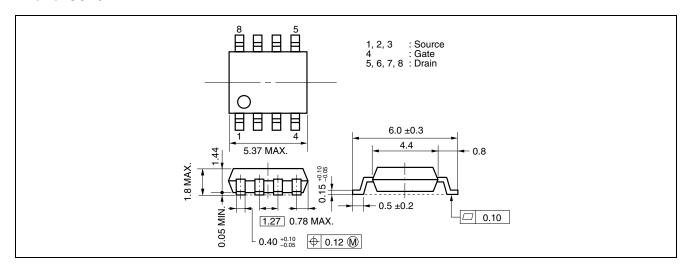
 $V_{\text{F(S-D)}}$ - Source to Drain Voltage - V

V_{GS} - Gate to Source Voltage - V

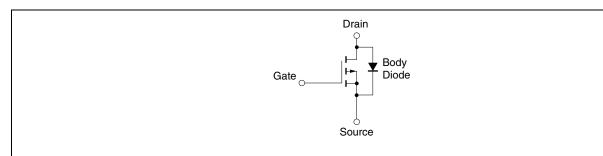
I_F - Diode Forward Current - A

Package Drawings (Unit: mm)

Power SOP8



Equivalent Circuit



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Revision History

μ PA2737GR Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Aug 28, 2012	-	First Edition Issued	

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